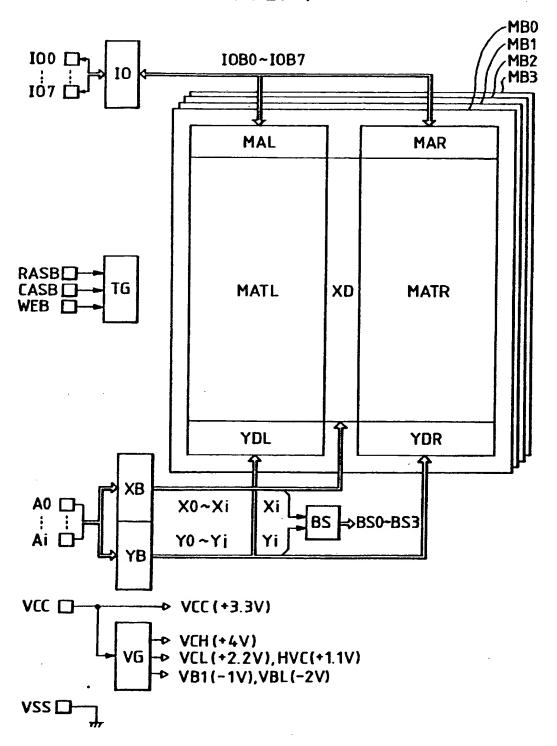
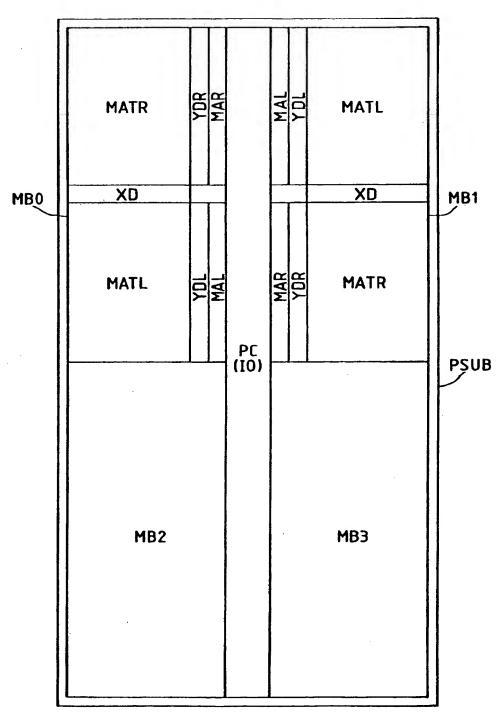
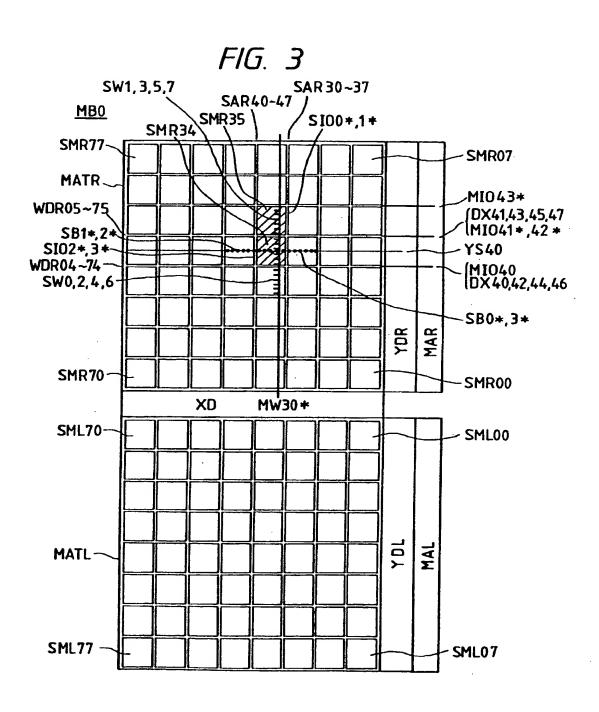
F/G. 1



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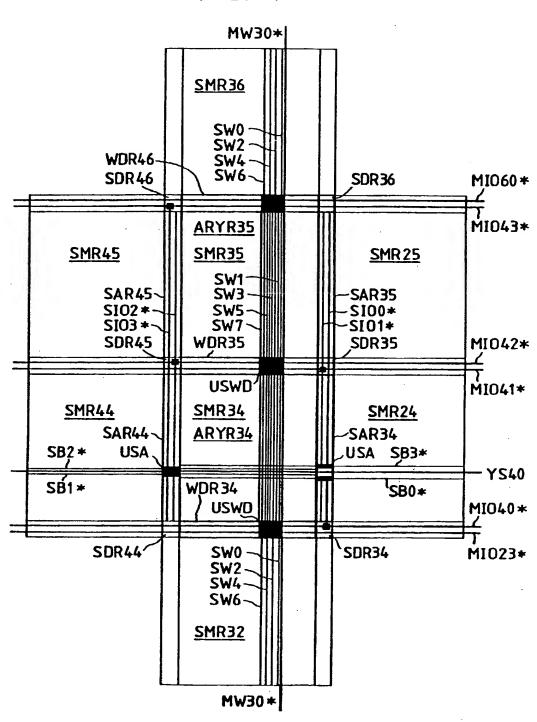
FIG. 2





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FIG. 4



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FIG. 5 SI02\* \*0EWM **SI00**\* \$103\***\*** SW7 SW5 SW3 SW1 A SI01\* 夺 **#MIO42** DX41, 43,45,47 US US us lus k WD WD WD WD WDR35 **SDR45**-SDR35 **4MIO41**\* SB254\* USA **USA SB255 ∀YS463** 4 SB253 \* USA **USA** #SB252\* SAR44~ ARYR34 SAR34 USA USA <del>ወወወወወወ</del> #SB3\* SB2 \* 4 SB1 \* #-USA USA **⇔** SB0 **∗ ⇔**MI040\* SH4R<sup>A</sup> <sup>∆</sup>SH3L US US US l us k DX40, 42,44,46 WD WD WD WD -SH4L, SDR44 SDR34 SH3R WDR34 **₽MI023**\* \*E012 SMR34 SW6 SW4 SW2 SWO MW30\*

母: MEMORY CELL 中, 中: SWITCH

TOGING TOTEOT

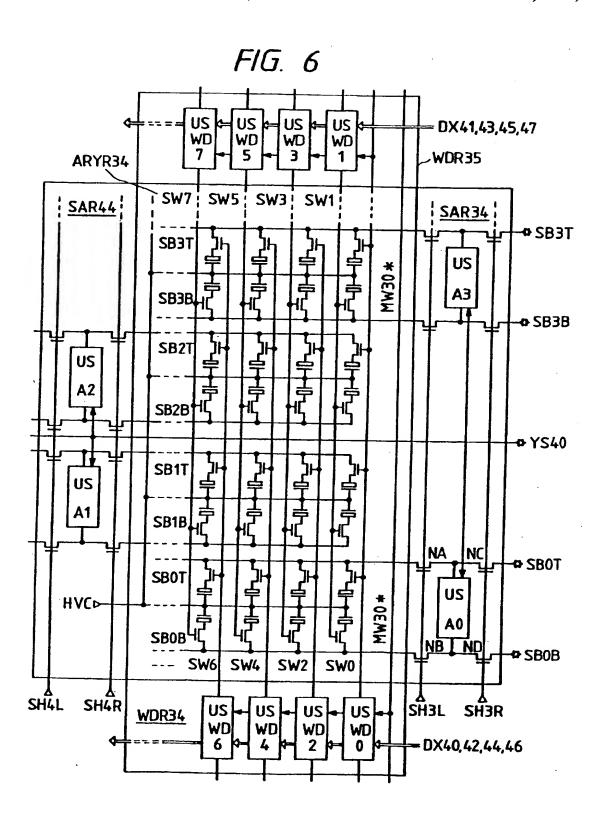
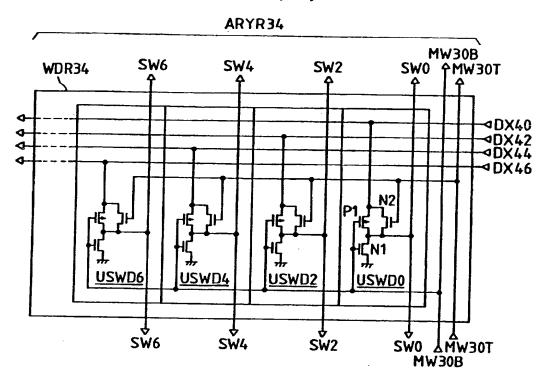


FIG. 7(A)



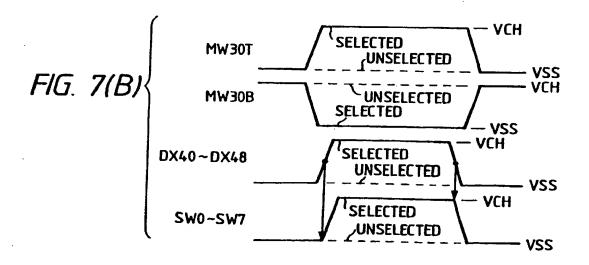
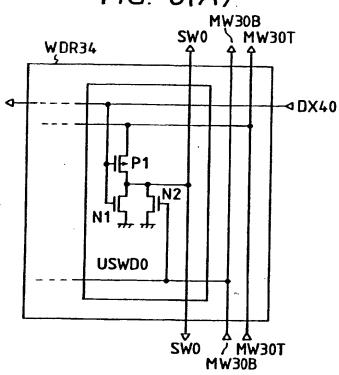
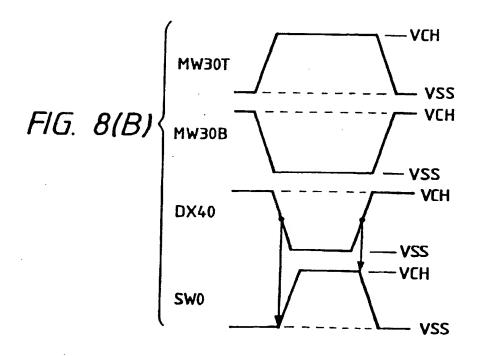


FIG. 8(A)

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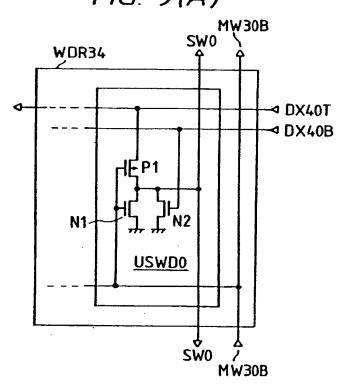


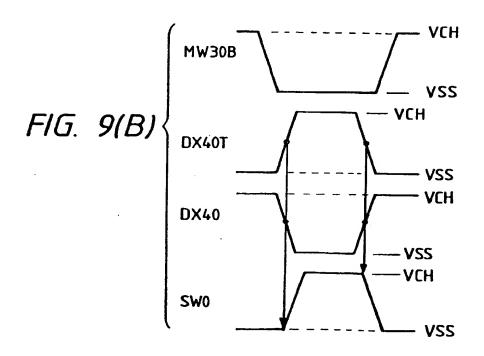
Oct. 12, 1999

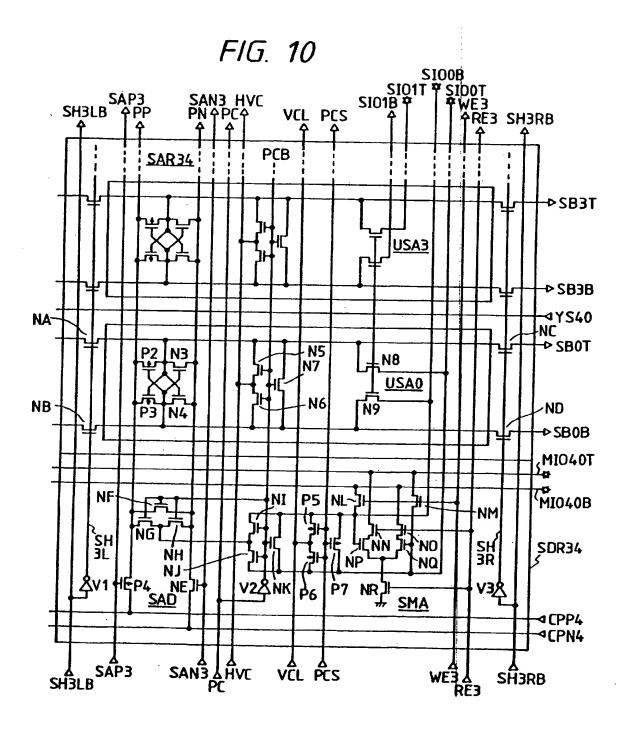
Sheet 9 of 22

5,966,341

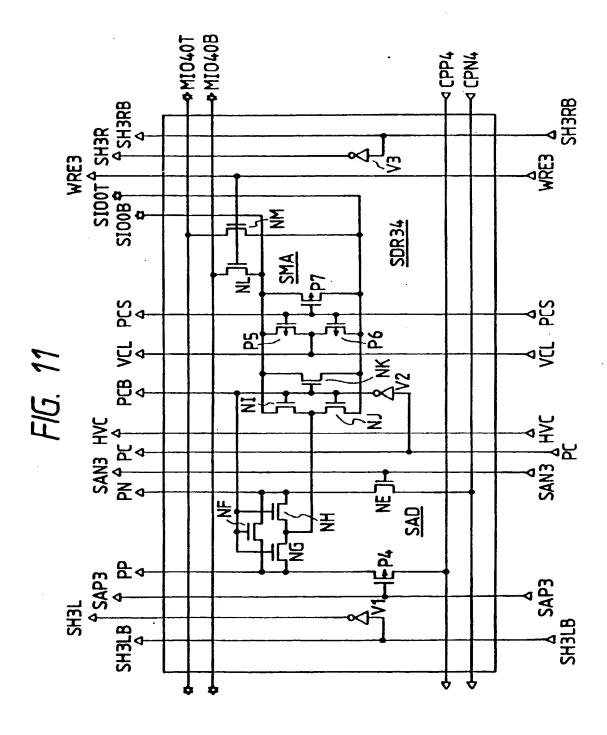
FIG. 9(A)







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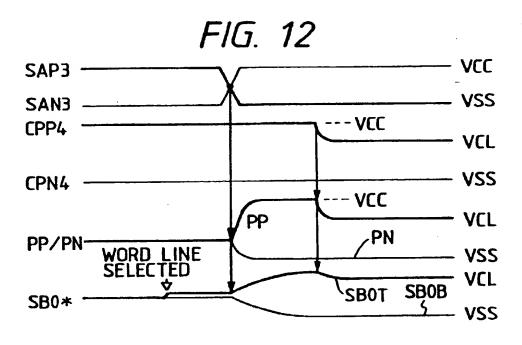
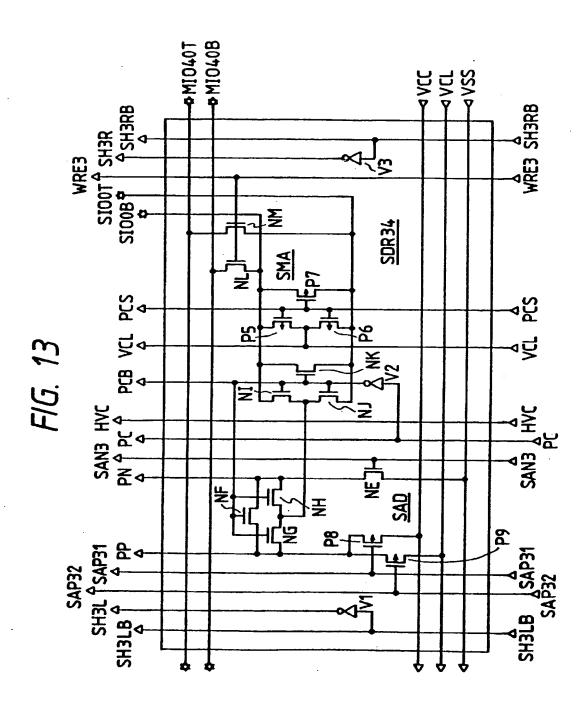
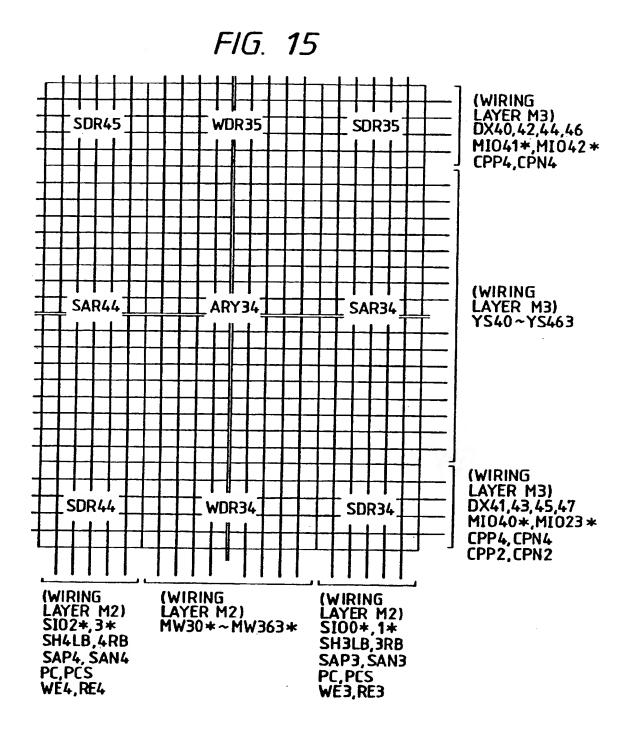


FIG. 14 VCC **SAP31** -**VSS SAN3** -VCC SAP32 VSS - VCC PP **VCL** PN PP/PN WORD LINE SELECTED **VSS** VCL SB0B SBOT SB0\* **VSS** 

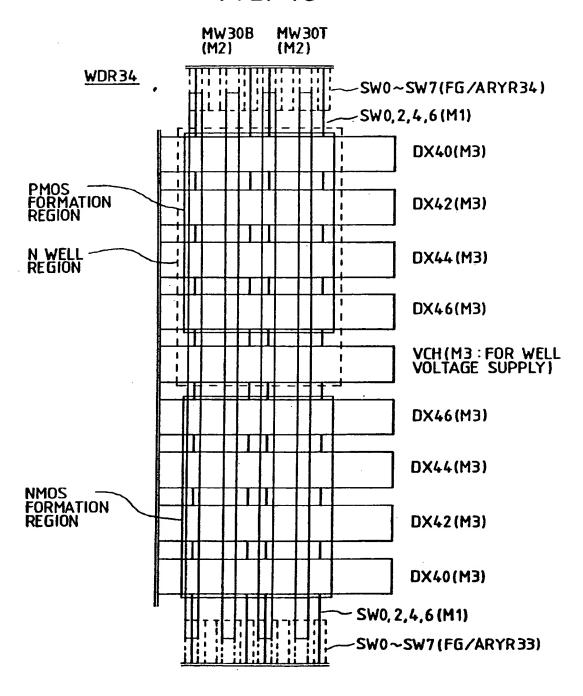


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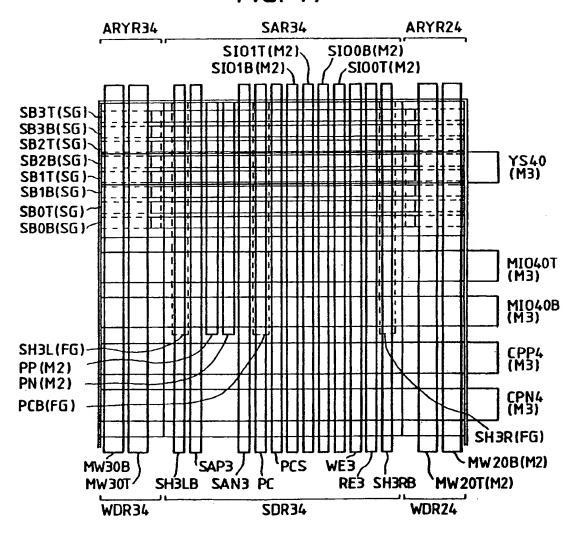
OSSYMBE INTEGE

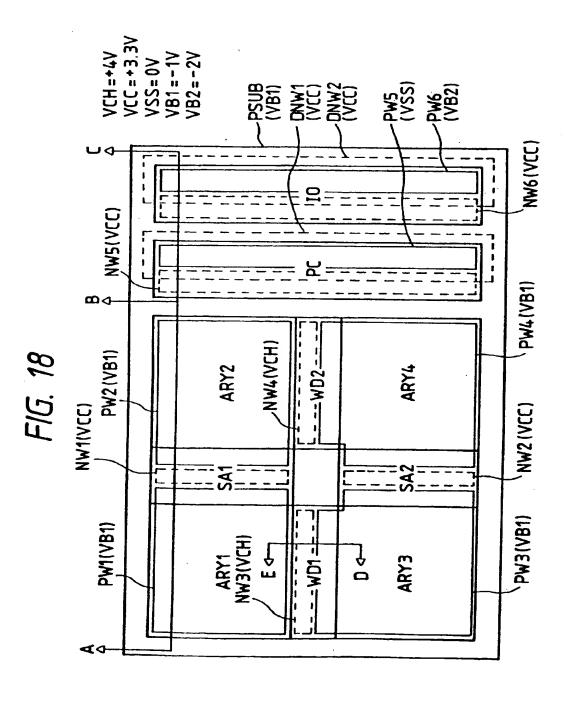
FIG. 16

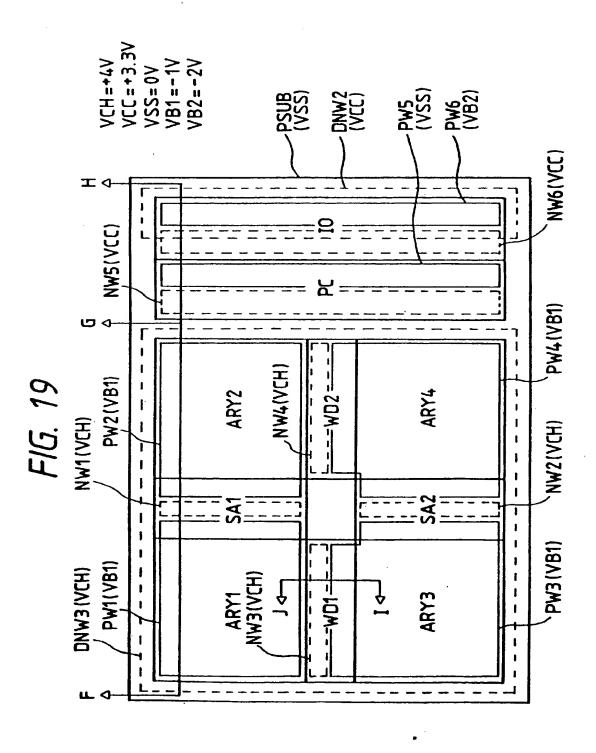


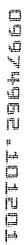
DOSTAGE TOTECT

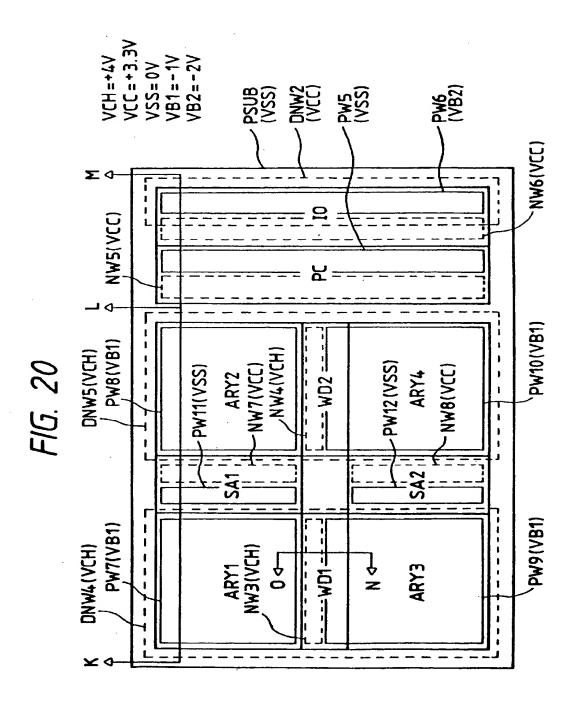
FIG. 17

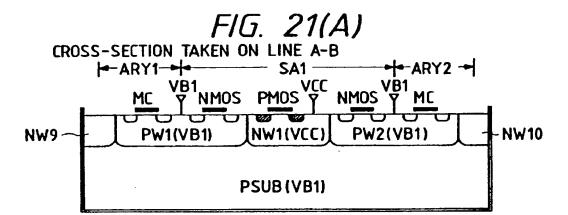


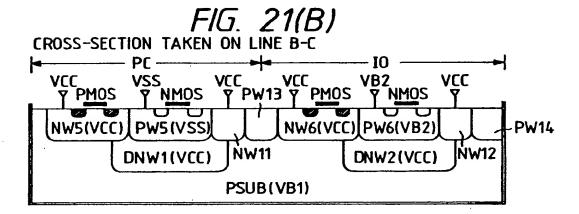


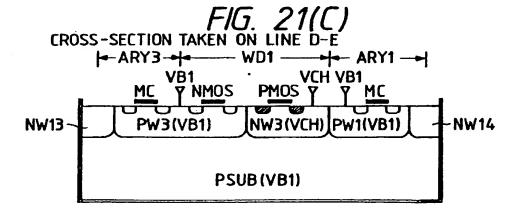




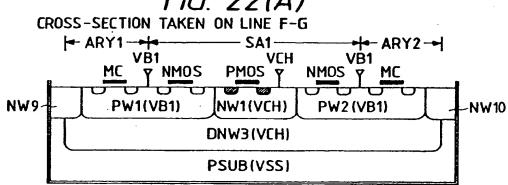


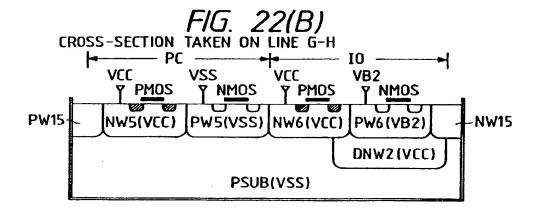


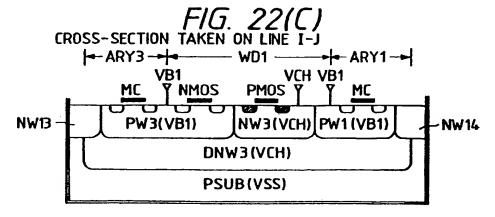




P+ DIFFUSION D: N+ DIFFUSION LAYER VCH=+4V VCC=+3.3V VSS=0V VB1=-1V VBB=-2V



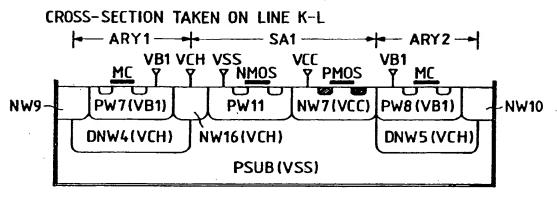


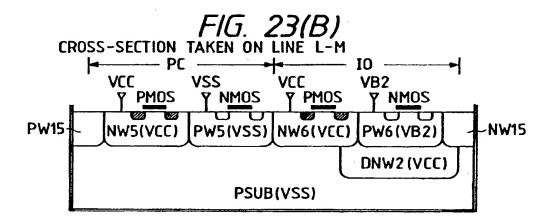


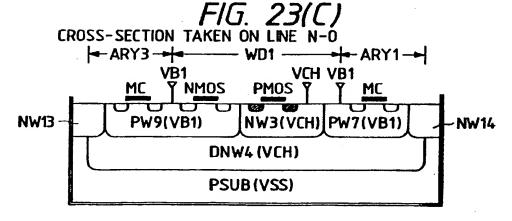
P\* DIFFUSION C:N\* DIFFUSION LAYER LAYER

VCH=+4V VCC=+3.3V VSS=0V VB1=-1V VBB=-2V

## FIG. 23(A)







P+ DIFFUSION D:N+ DIFFUSION LAYER LAYER VCH=+4V VCC=+3.3V VSS=0V VB1=-1V VBB=-2V

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